NSN 5961-01-012-1945

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-012-1945 **Inclosure Material:** Glass **Overall Length:** 0.300 inches **Terminal Length:** 1.000 inches **Overall Diameter:** 0.107 inches Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-7 **Mounting Method: Terminal Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 30.0 working peak reverse voltage, peak total value **Power Rating Per Characteristic:** 400.0 milliwatts small-signal input power, common-collector preset **Capacitance Rating In Picofarads:** 18.0 **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius ambient air **Precious Material And Location:** Terminal surface option gold **Precious Material:** Gold **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 uninsulated wire lead **Specification Data:** 81349-mil-s-19500/436 government specification Shelf Life: N/a **Unit Of Measure:**

No

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Demilitarization: